



P-Channel 12-V (D-S) MOSFET

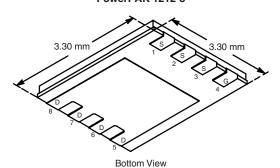
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 12	0.016 at V _{GS} = - 4.5 V	- 12.6		
	0.022 at $V_{GS} = -2.5 \text{ V}$	- 10.8		
	0.029 at V _{GS} = - 1.8 V	- 3.5		

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFETS: 1.8 V Rated
- New PowerPAK[®] Package
 - Low Thermal Resistance, RthJC
 - Low 1.07 mm Profile

ROHS COMPLIANT HALOGEN FREE

PowerPAK 1212-8

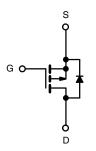


Ordering Information: Si7425DN-T1-E3 (Lead (Pb)-free)

Si7425DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- · Load Switch
- PA Switch
- Battery Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 12		V	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Dusin Comment /T 150 °C\\	T _A = 25 °C	- I _D	- 12.6	- 8.3		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 9.1	- 6.0	^	
Pulsed Drain Current		I _{DM}	- 25		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 3.0	- 1.3		
Mariana Dana Disabaliana	T _A = 25 °C	- P _D	3.6	1.5	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.9	0.8	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{b, c}			260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian de Ambienta	t ≤ 10 s	R _{thJA}	28	35	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		65	81		
Maximum Junction-to-Case	Steady State	R_{thJC}	2.9	3.8		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (www.vishay.com/ppg?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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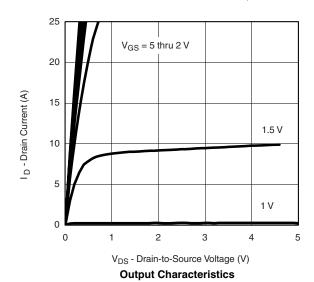
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			•	•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -300 \mu A$	- 0.40		- 1.0	V	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V			- 1	μΑ	
		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 85 °C			- 5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 25			Α	
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 12.6 A		0.013	0.016		
	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 10.8 A		0.017	0.022	Ω	
		V _{GS} = - 1.8 V, I _D = - 3.5 A		0.023	0.029		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 6 V, I _D = - 12.6 A		38		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 3.0 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			26	39		
Gate-Source Charge	Q_{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -12.6 \text{ A}$		4.1		nC	
Gate-Drain Charge	Q_{gd}			7.0			
Gate Resistance	R_{g}	f = 1 MHz		5.0		Ω	
Turn-On Delay Time	t _{d(on)}			30	45		
Rise Time	t _r	V_{DD} = - 6 V, R_L = 6 Ω		55	75		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		130	260	ns	
Fall Time	t _f			100	225		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 3.2 A, dl/dt = 100 A/μs		52	80		

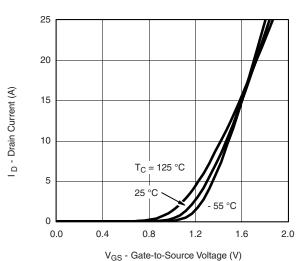
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





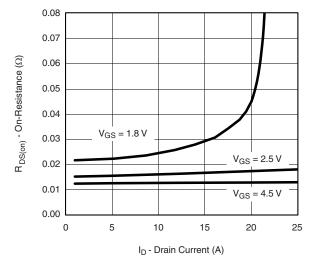
Transfer Characteristics



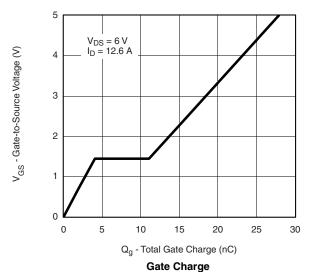


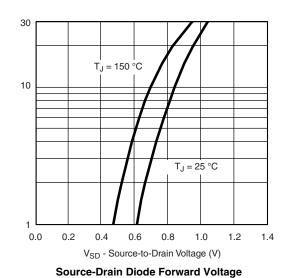


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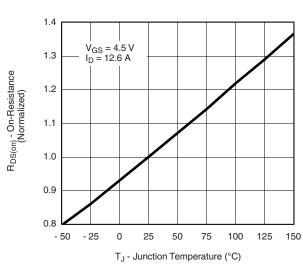
On-Resistance vs. Drain Current



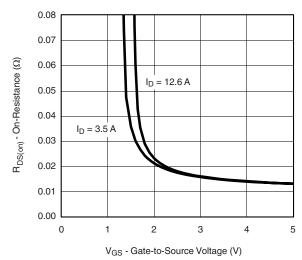


4000 3200 C_{iss} C - Capacitance (pF) 2400 1600 C_{oss} 800 C_{rss} 0 2 6 8 12 0 10 V_{DS} - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature



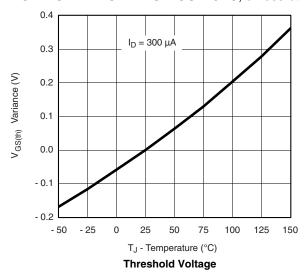
On-Resistance vs. Gate-to-Source Voltage

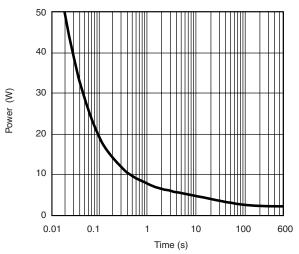
Is - Source Current (A)

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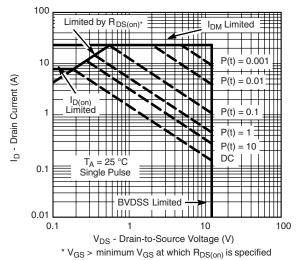
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

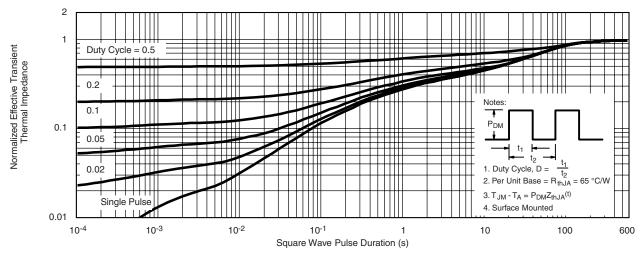




Single Pulse Power, Junction-to-Ambient



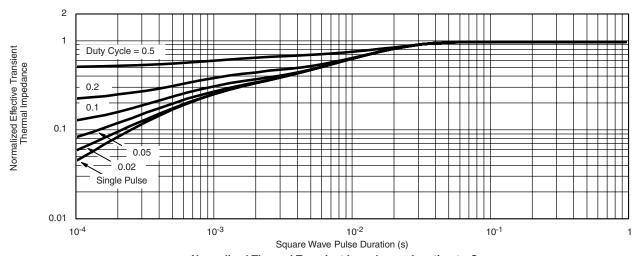




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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